AON2803

20V Dual P-Channel MOSFET

General Description

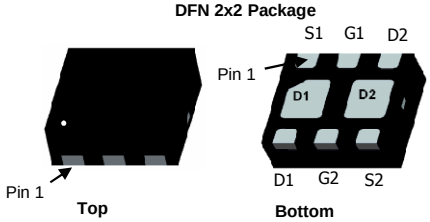
The AON2803 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltage as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

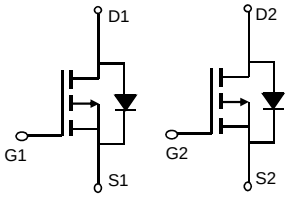
Product Summary

V_{DS}	-20V
I_D (at V_{GS}=-4.5V)	-3.8A
$R_{DS(ON)}$ (at V_{GS}=-4.5V)	< 70mΩ
$R_{DS(ON)}$ (at V_{GS} =-2.5V)	< 90mΩ
$R_{DS(ON)}$ (at V_{GS} =-1.8V)	< 115mΩ

Green Product

DFN 2x2 Package





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current	T_A=25°C	I_D	-3.8	A
	T_A=70°C		-3	
Pulsed Drain Current [C]		I_{DM}	-20	
Power Dissipation [A]	T_A=25°C	P_D	1.5	W
	T_A=70°C		0.95	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	35	45	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		65	85	°C/W
Maximum Junction-to-Ambient [B]	t ≤ 10s	$R_{\theta JA}$	120	155	°C/W
Maximum Junction-to-Ambient [B]	Steady-State		175	235	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250µA	-0.4	-0.6	-1	V
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V	-20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V, I_D=-3.8A		58	70	mΩ
		T_J=125°C		78	94	
		V_{GS}=-2.5V, I_D=-3A		70	90	mΩ
		V_{GS}=-1.8V, I_D=-2A		85	115	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-3.8A		15		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.66	-1	V
I_S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-10V, f=1MHz		560		pF
C_{oss}	Output Capacitance			80		pF
C_{rss}	Reverse Transfer Capacitance			70		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		15	30	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-10V, I_D=-3.8A		8.5	12	nC
Q_{gs}	Gate Source Charge			1.2		nC
Q_{gd}	Gate Drain Charge			2.1		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-4.5V, V_{DS}=-10V, R_L=2.6Ω, R_{GEN}=3Ω		7.2		ns
t_r	Turn-On Rise Time			36		ns
$t_{D(off)}$	Turn-Off DelayTime			53		ns
t_f	Turn-Off Fall Time			56		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-3.8A, dI/dt=100A/µs		37		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-3.8A, dI/dt=100A/µs		27		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150° C.

B. The value of $R_{\theta JA}$ is measured with the device mounted on a minimum pad board. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150° C.

C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

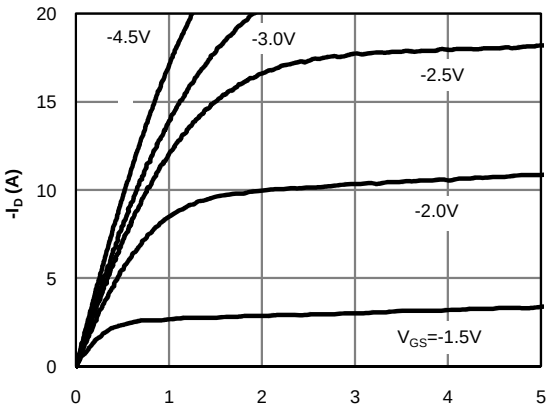


Fig 1: On-Region Characteristics

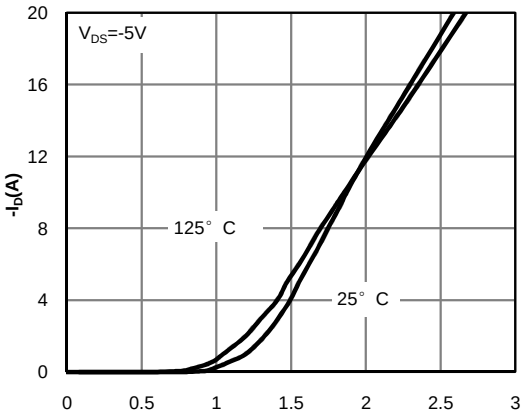


Figure 2: Transfer Characteristics

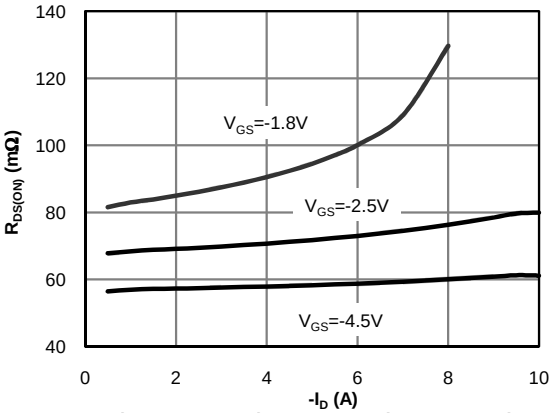


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

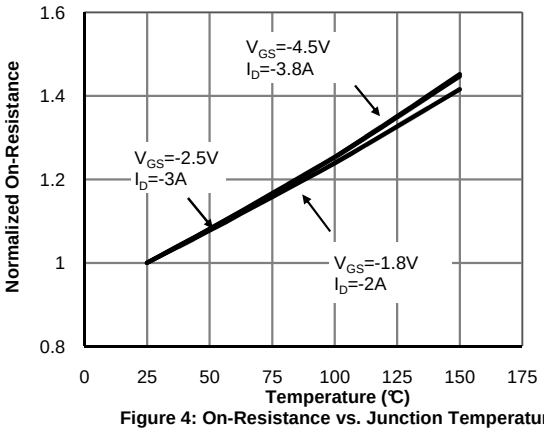


Figure 4: On-Resistance vs. Junction Temperature

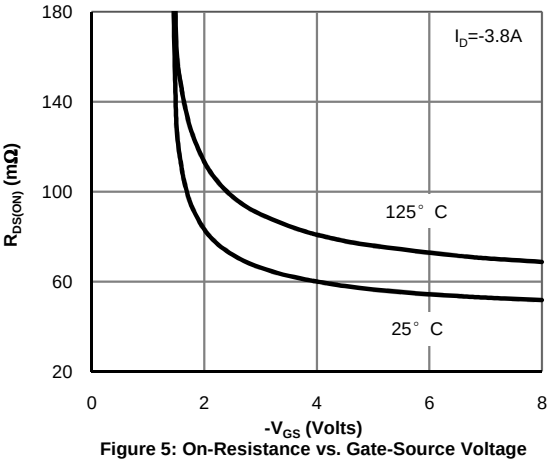


Figure 5: On-Resistance vs. Gate-Source Voltage

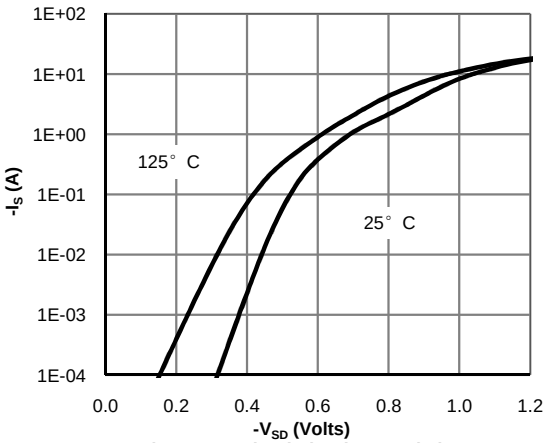


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

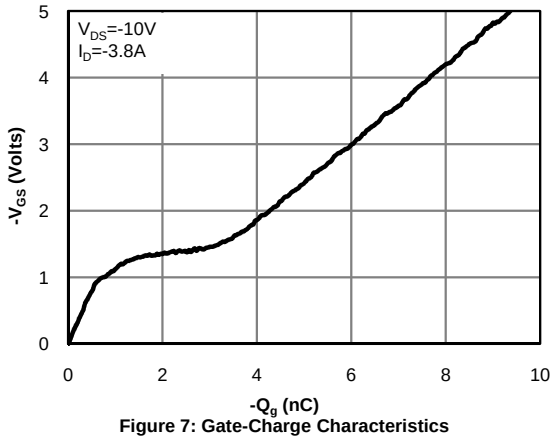


Figure 7: Gate-Charge Characteristics

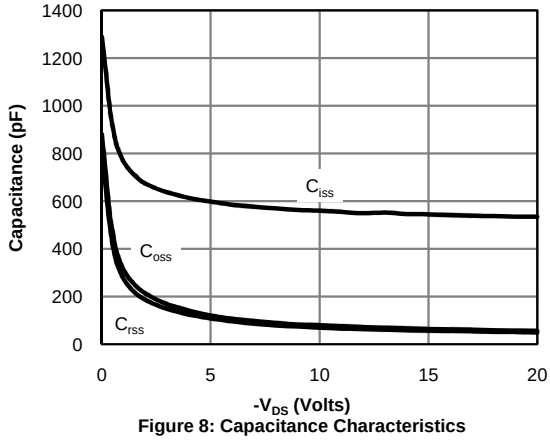


Figure 8: Capacitance Characteristics

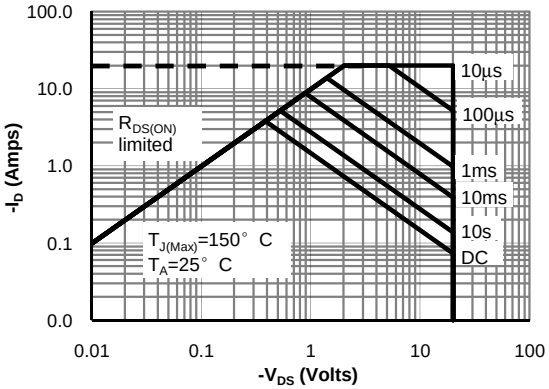


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

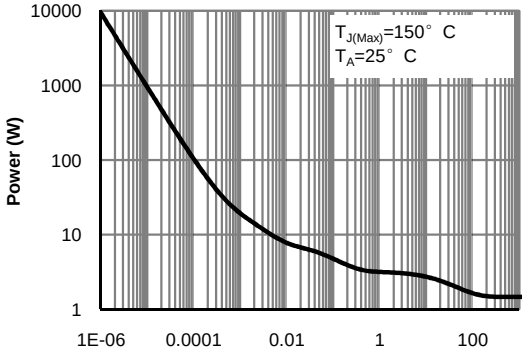


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

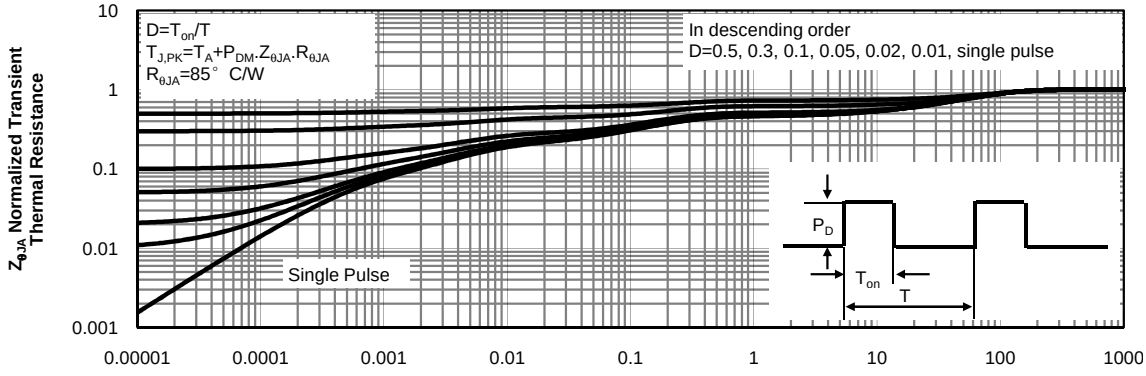
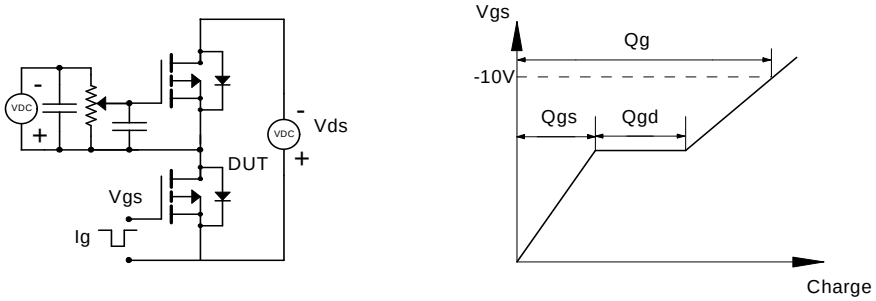
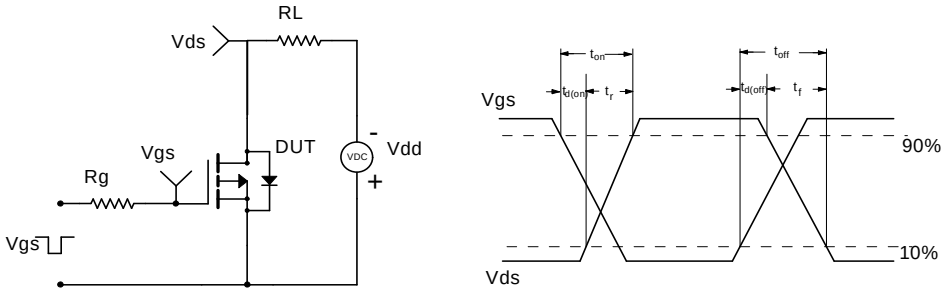


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms